

SMD Type

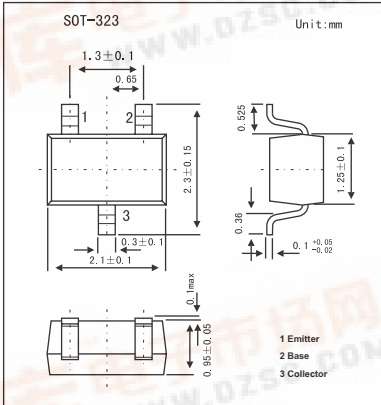
Transistors

High-voltage Amplifier Transistor

2SC4102

■ Features

- High breakdown voltage.(VCEO = 120V)



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	120	V
Collector-emitter voltage	V _{CEO}	120	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _c	50	mA
Collector power dissipation	P _c	0.2	W
Junction temperature	T _j	150	℃
Storage temperature	T _{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _c =50μA	120			V
Collector-emitter breakdown voltage	V _{CEO}	I _c =1mA	120			V
Emitter-base breakdown voltage	V _{EB0}	I _E =50μA	5			V
Collector cutoff current	I _{cBO}	V _{CB} =100V			0.5	μ A
Emitter cutoff current	I _{EBO}	V _{EB} =4V			0.5	μ A
DC current transfer ratio	h _{FE}	V _{CE} =6V, I _c =2mA	180		560	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =10mA, I _B =1mA			0.5	V
Output capacitance	C _{ob}	V _{CB} =12V, I _E =0A, f=1MHz		2.5		pF
Transition frequency	f _T	V _{CE} =-12V, I _E = 2mA, f=100MHz		140		MHz

■ hFE Classification

Marking	TR	TS
Rank	R	S
hFE	180~390	270~560

